

Features

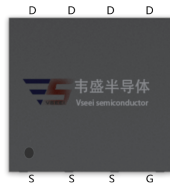
- Ultra-low $R_{DS(ON)}$
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Applications

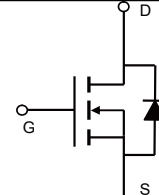
- Power Mgmt. in Computing, CE, Digital Lifestyle, IE 4.0, Communications
- Current Switching in DC/DC (H-bridge, Buck/Boost) & AC/DC (Inverting, SR)
- Load Switching over V_{BUS} in Fast Charger, Half-bridging in Wireless Charger
- Motor Driving in Home Appliance, Robotics, Ventilation

Product Summary

Parameter	Value	Unit
V_{DS}	30	V
$V_{GS(th)}$ _Typ	1.7	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	43	A
$R_{DS(ON)}$ _Typ (@ $V_{GS} = 10V$)	7.0	m Ω
$R_{DS(ON)}$ _Typ (@ $V_{GS} = 4.5V$)	10.6	m Ω



DFN3x3



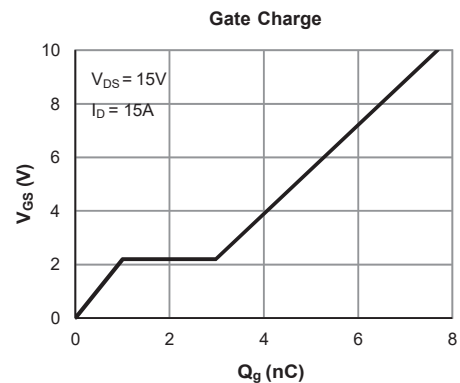
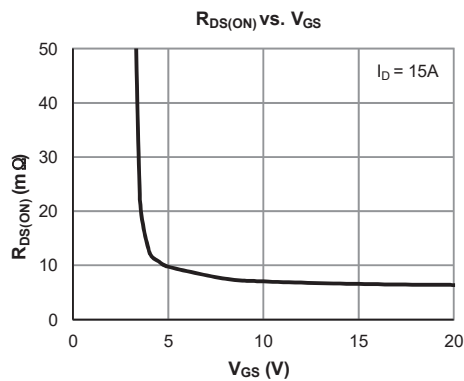
Schematic

Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
VSM43N03-D33	DFN3x3	8	VSM43N03	1	-55 to 150	13-inch Reel	5000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ\text{C}$	43
		$T_C = 100^\circ\text{C}$	27
Pulsed Drain Current ⁽²⁾	I_{DM}	156	A
Avalanche Current ⁽³⁾	I_{AS}	13	A
Avalanche Energy ⁽³⁾	E_{AS}	8.5	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ\text{C}$	26
		$T_C = 100^\circ\text{C}$	10
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



Electrical Characteristics (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2	1.7	2.5	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 15\text{A}$		7.0	8.8	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 10\text{A}$		10.6	13.8	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}, I_D = 15\text{A}$		48		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.68	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			26	A

DYNAMIC PARAMETERS ⁽⁵⁾

Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}, f = 1\text{MHz}$		468		pF
Output Capacitance	C_{oss}			363		pF
Reverse Transfer Capacitance	C_{rss}			41		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		3.3		Ω

SWITCHING PARAMETERS ⁽⁵⁾

Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 15\text{V}, I_D = 15\text{A}$		7.7		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$)	Q_g			4.4		nC
Gate Source Charge	Q_{gs}			1.0		nC
Gate Drain Charge	Q_{gd}			2.0		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 15\text{V}$ $R_L = 1.0\text{ }\Omega, R_{GEN} = 6\text{ }\Omega$		2.7		ns
Turn-On Rise Time	t_r			3.5		ns
Turn-Off DelayTime	$t_{D(off)}$			12.5		ns
Turn-Off Fall Time	t_f			5.8		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		16.6		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 15\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		5.5		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	R_{JA}	50	65	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	R_{JC}	4.0	4.8	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. This single-pulse measurement was taken under the following condition [$L = 100\text{ }\mu\text{H}, V_{GS} = 10\text{V}, V_{DS} = 30\text{V}$] while its value is limited by $T_{J_Max} = 150^\circ\text{C}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

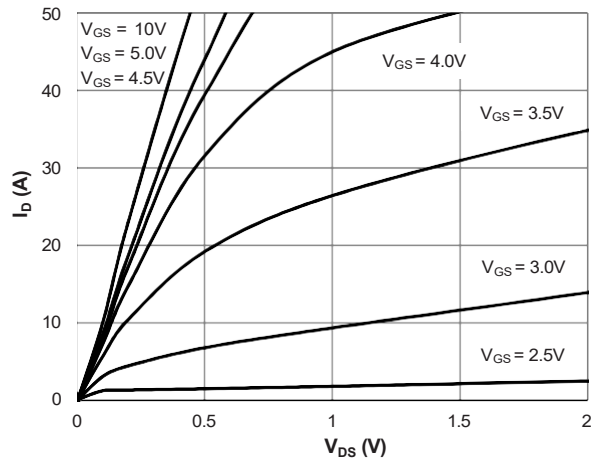


Figure 1: Saturation Characteristics

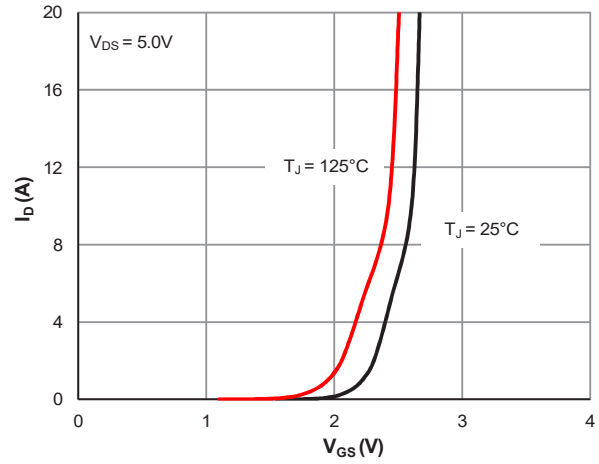


Figure 2: Transfer Characteristics

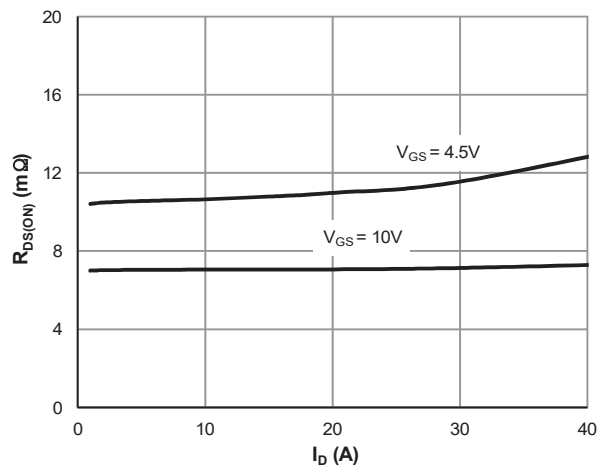


Figure 3: $R_{DS(ON)}$ vs. Drain Current

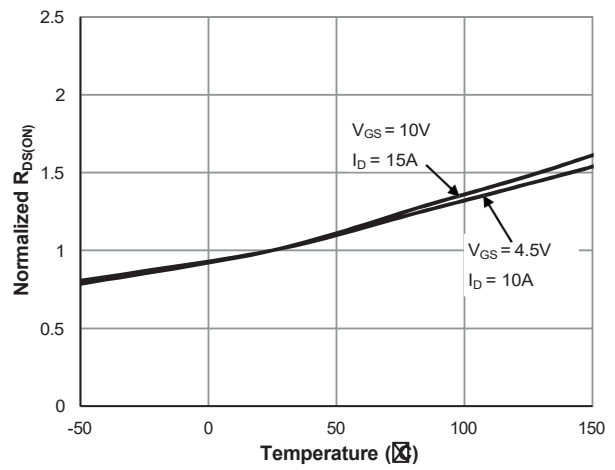


Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

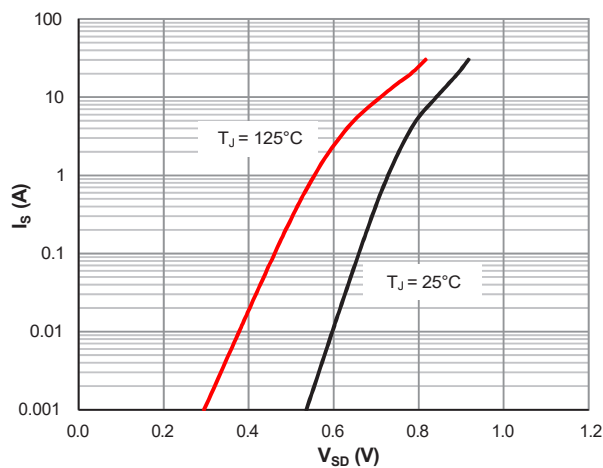


Figure 5: Body-Diode Characteristics

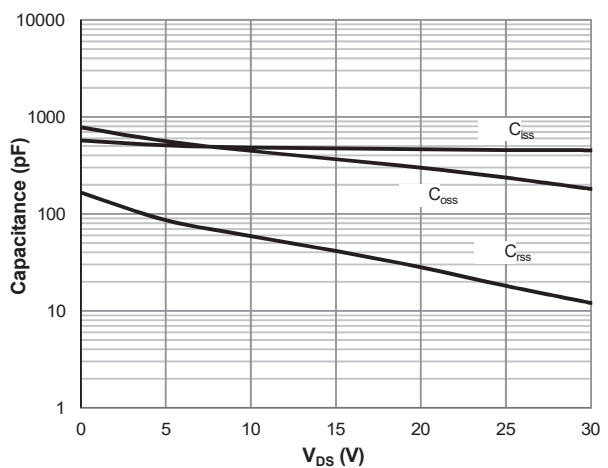


Figure 6: Capacitance Characteristics

Typical Electrical & Thermal Characteristics

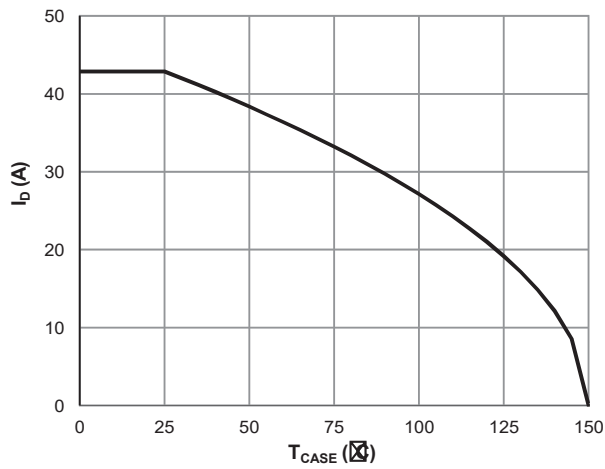


Figure 7: Current De-rating

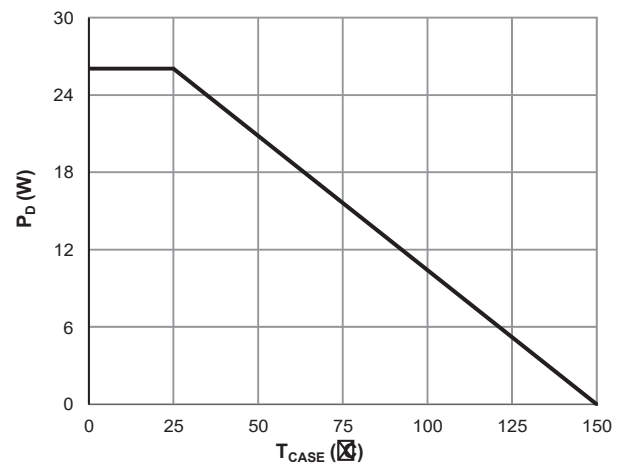


Figure 8: Power De-rating

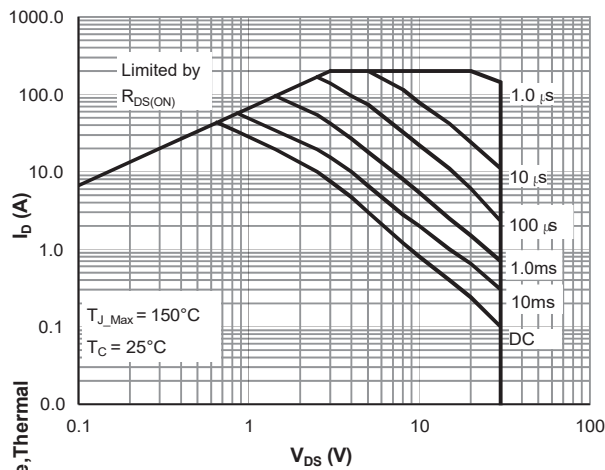


Figure 9: Maximum Safe Operating Area

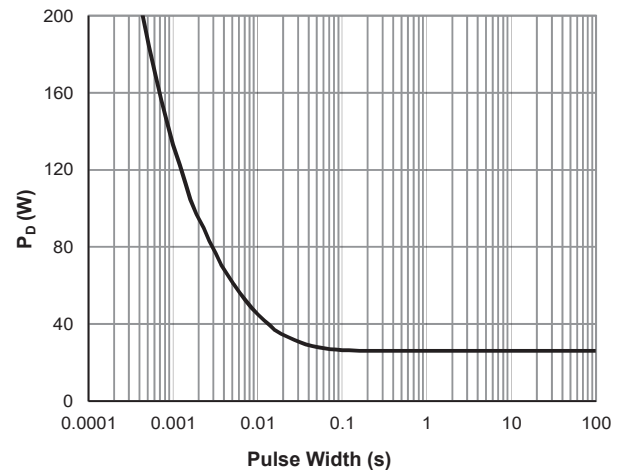


Figure 10: Single Pulse Power Rating, Junction-to-Case

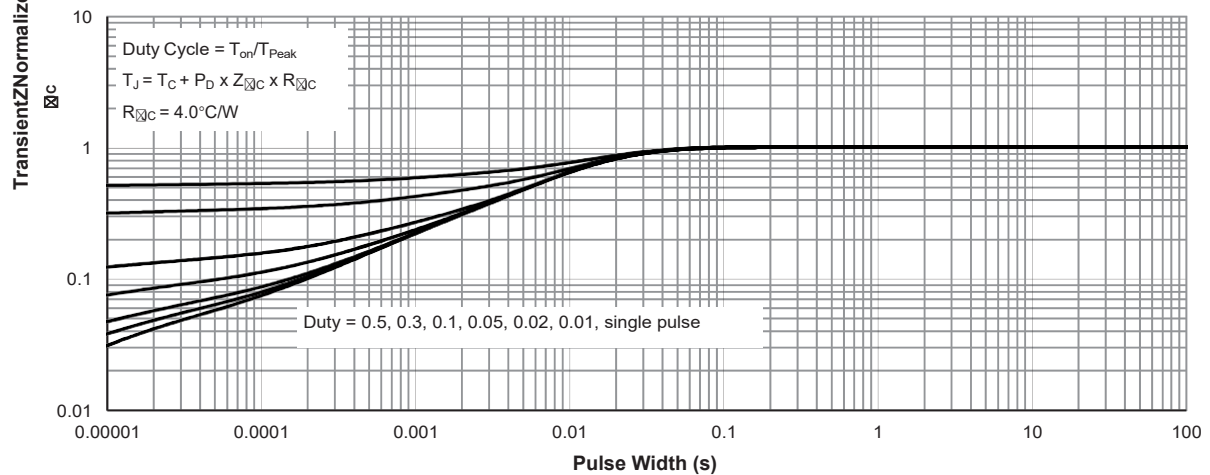


Figure 11: Normalized Maximum Transient Thermal Impedance